



HUIZHOU JINSANE ELECTRONICS CO., LTD

JINSANE

SOD-123 Plastic-Encapsulate Diodes

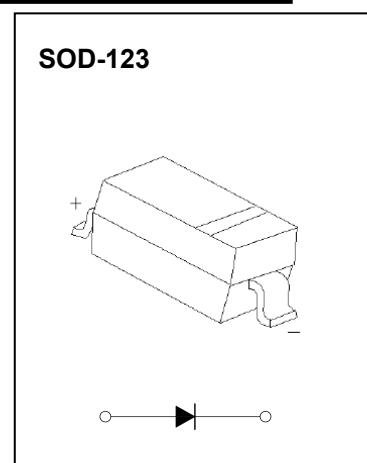
B5819W

SCHOTTKY BARRIER DIODE

FEATURES

For use in low voltage, high frequency inverters
Free wheeling, and polarity protection applications.

MARKING: **S4**



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	B5819W		Unit
Non-Repetitive Peak Reverse Voltage	V _{RM}	40		V
Peak Repetitive Peak Reverse Voltage	V _{RRM}			
Working Peak Reverse Voltage	V _{RWM}	40		V
DC Blocking Voltage	V _R			
RMS Reverse Voltage	V _{R(RMS)}	28		V
Average Rectified Output Current	I _o	0.35		A
Peak Forward Surge Current @t=8.3ms	I _{FSM}	2		A
Repetitive Peak Forward Current	I _{FRM}	0.5		A
Power Dissipation	P _d	400		mW
Thermal Resistance Junction to Ambient	R _{θJA}	20		°C/W
Storage Temperature	T _{STG}	- 65 — +125		°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V _(BR)	I _R = 1mA B5819W	40		V
Reverse voltage leakage current	I _R	V _R V _R =40V B5819W		5	uA
Forward voltage	V _F	B5819W I _F =0.35A I _F =2A		0.37 0.6	V
Diode capacitance	C _D	V _R =0V, f=1MHz		50	pF

Typical Characteristics

B5819W

